

## **Description**

The FDMS8880 uses advanced trench technology to provide excellent R<sub>DS(ON)</sub>, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

#### **General Features**

V<sub>DS</sub> = 30V I<sub>D</sub> =50A

 $R_{DS(ON)} < 8.5 m\Omega V_{GS} = 10V$ 

## **Application**

Battery protection

Load switch

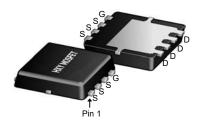
Uninterruptible power supply

## Package Marking and Ordering Information

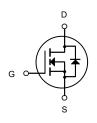
Product ID	Pack	Brand	Qty(PCS)
FDMS8880	DFN5X6-8L(Power-56-8)	HXY MOSFET	5000

## Absolute Maximum Ratings (Tc=25 ℃ unless otherwise noted)

Symbol	Parameter	Rating	Units		
VDS	Drain-Source Voltage	30	V		
Vgs	Gate-Source Voltage	±20			
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	А			
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup> 38			
Ірм	Pulsed Drain Current <sup>2</sup>	200	А		
EAS	Single Pulse Avalanche Energy <sup>3</sup>	36	mJ		
las	Avalanche Current	50	А		
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	31	W		
Тѕтс	Storage Temperature Range	-55 to 150	°C		
TJ	Operating Junction Temperature Range	-55 to 150	°C		
Reja	Thermal Resistance Junction-Ambient <sup>1</sup>	62	°C/W		
Rejc	Thermal Resistance Junction-Case <sup>1</sup>	27	°C/W		



DFN5X6-8L (Power-56-8)



N-Channel MOSFET



## Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Тур	Max	Units	
BV <sub>DSS</sub>	Drain-Sourtce Breakdown Voltage	V <sub>GS</sub> =0V,I <sub>D</sub> =250 μ A	30			V	
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>GS</sub> =0V, V <sub>DS</sub> =24V			1	μA	
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ = $\pm$ 20V, $V_{DS}$ =0A			±100	nA	
$V_{GS(th)}$	GATE-Source Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250 μ A	1.2	1.5	2.5	V	
	Drain-Source On Resistance <sup>2</sup>	V <sub>GS</sub> =10V,I <sub>D</sub> =30A		6.5	8.5	8.5 m Ω	
R <sub>DS(ON)</sub>		V <sub>GS</sub> =4.5V,I <sub>D</sub> =15A		11	14		
G <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> =5V, I <sub>D</sub> =30A		38		S	
C <sub>iss</sub>	Input Ca pacitance			1317	1844	pF	
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1MHz		163	228		
C <sub>rss</sub>	Re verse Transfer Capacitance			131	183		
t <sub>d(on)</sub>	Turn-On Delay Time			4.6	9.2	ns	
t <sub>r</sub>	RiseTime	$V_{DD}=15V,I_{D}=15A,R_{L}=\Omega$		12.2	22	ns	
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS}$ =15V, $R_{G}$ =3.3 $\Omega$		26.6	53	ns	
t <sub>f</sub>	FallTime			8	16	ns	
$\mathbf{Q}_{\mathrm{g}}$	Total Gate Charge			21	17.6	nC	
$\mathbf{Q}_{gs}$	Gate-Source Charge	V <sub>GS</sub> =4.5V, V <sub>DS</sub> =15V,		2.35	5.9	nC	
$\mathbf{Q}_{gd}$	Gate-Drain "Miller" Charge	I <sub>D</sub> =15A		5.9	7.1	nC	
$V_{SD}$	Source-Drain Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V,I <sub>S</sub> =1A			1	٧	
IS	Continuous Source Current1.5	VG=VD=0V , Force			58	Α	
ISM	Pulsed Source Current 2.5	Current			115	Α	
trr	Reverse Recovery Time	IF=30A,		9.2			
Qrr	Reverse Recovery Charge	dI/dt=100A/¦ÌsTJ=25°C		2			



## **Typical Characteristics**

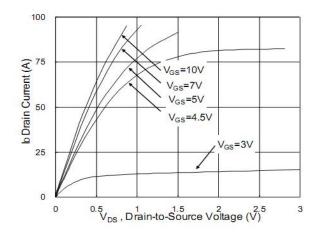
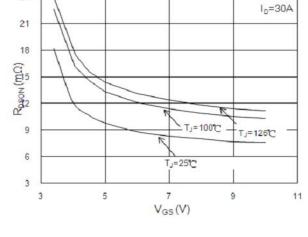


Fig. 1 Typical Output Characteristics



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Fig. 2 On-Resistance vs. Gate-Source

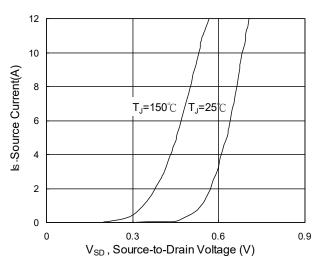


Fig.3 Forward Characteristics of reverse

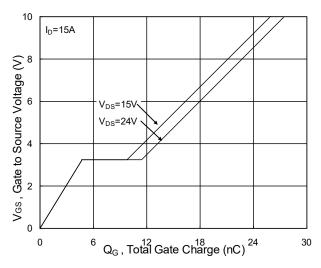


Fig.4 Gate-Charge Characteristics

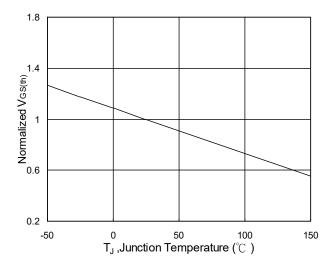


Fig.5 Normalized V<sub>GS(th)</sub> vs. T<sub>J</sub>

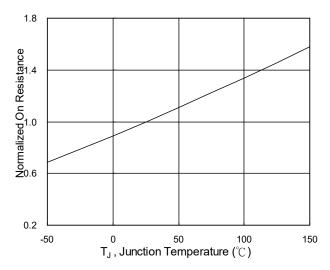
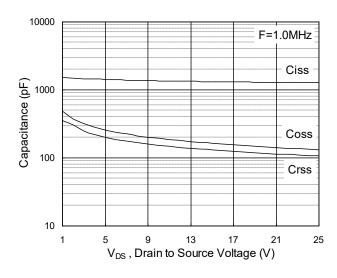


Fig.6 Normalized R<sub>DSON</sub> vs. T<sub>J</sub>





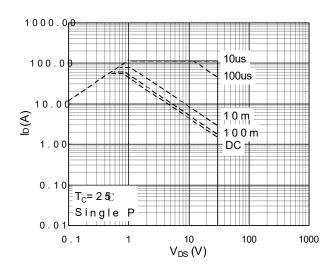
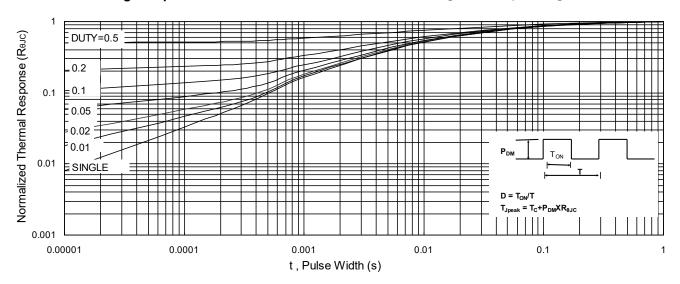
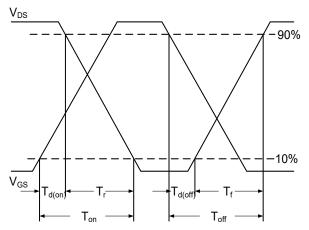
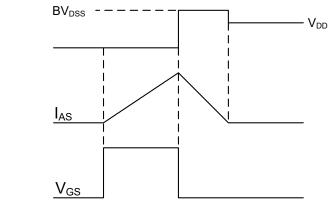


Fig.7 Capacitance

Fig.8 Safe Operating Area





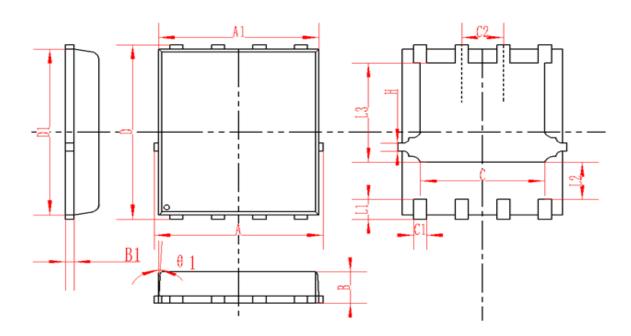


EAS=  $\frac{D}{2}$ L x I<sub>AS</sub> x  $\frac{D}{BV_{DSS}-V_{DD}}$ 

Fig.10 Switching Time Waveform



# DFN5X6-8L(Power-56-8)Package Information



SYMBOL	MM		INCH			
	MIN	NOM	MAX	MIN	NOM	MAX
Α	5.3	5.5	5.7	0.208	0.216	0.224
A1	5.1	5.2	5.3	0.2	0.204	0.209
D	5.98	6	6.02	0.235	0.236	0.237
D1	5.85	6.05	6.25	0.23	0.238	0.246
В	0.85	0.95	1.05	0.033	0.037	0.041
B1	0.254REF		0.010REF			
С	3.95	4	4.05	0.156	0.157	0.159
C1	0.35	0.4	0.45	0.014	0.016	0.018
C2		1.27TYP			0.5TYP	
θ1	8°	10°	12°	8°	10°	12°
L1	0.63	0.64	0.65	0.025	0.025	0.026
L2	1.2	1.3	1.4	0.047	0.051	0.055
L3	3.415	3.42	3.425	0.134	0.135	0.135
Н	0.24	0.25	0.26	0.009	0.010	0.010



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